

## Low Noise Silicon Bipolar RF Transistor

- High linearity low noise RF transistor
- 22 dBm OP1dB and 31 dBm OIP3
  @ 900 MHz, 8 V, 70 mA
- For UHF / VHF applications
- Driver for multistage amplifiers
- For linear broadband and antenna amplifiers
- Collector design supports 5 V supply voltage
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR106	R7s	1=B	2=E	3=C	SOT23

**Maximum Ratings** at  $T_A$  = 25 °C, unless otherwise specified

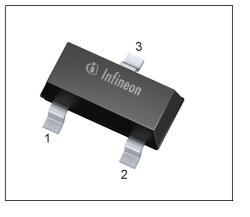
Parameter	Symbol	Value	Unit
Collector-emitter voltage,	V <sub>CEO</sub>		V
<i>T</i> <sub>A</sub> = 25°C		16	
<i>T</i> <sub>A</sub> = -55°C		15	
Collector-emitter voltage	V <sub>CES</sub>	20	
Collector-base voltage	V <sub>CBO</sub>	20	
Emitter-base voltage	V <sub>EBO</sub>	3	
Collector current	I <sub>C</sub>	210	mA
Base current	l <sub>B</sub>	21	
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	700	mW
<i>T</i> <sub>S</sub> ≤ 76 °C			
Junction temperature	TJ	150	°C
Storage temperature	T <sub>Stq</sub>	-55 150	

#### Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	105	K/W

 $^{1}T_{S}$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup>For calculation of  $R_{\text{thJS}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



2013-11-21



Parameter	Symbol	ol Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	15	-	-	V
I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0					
Collector-emitter cutoff current	I <sub>CES</sub>				μA
V <sub>CE</sub> = 20 V, V <sub>BE</sub> = 0		-	-	1	
$V_{\rm CE} = 10 \text{ V}, V_{\rm BE} = 0$		-	0.001	0.03	
Collector-base cutoff current	I <sub>CBO</sub>	-	1	30	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	1	30	
$V_{\rm EB} = 2 \text{ V}, I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					

# **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random samplin	<u>g)</u>				
Transition frequency	f <sub>T</sub>	3.5	5	-	GHz
<i>I</i> <sub>C</sub> = 70 mA, <i>V</i> <sub>CE</sub> = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.85	1.2	pF
$V_{\rm CB}$ = 10 V, f = 1 MHz, $V_{\rm BE}$ = 0,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.27	-	]
V <sub>CE</sub> = 10 V, <i>f</i> = 1 MHz, V <sub>BE</sub> = 0 ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	3.9	-	]
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,					
collector grounded					
Minimum noise figure	NF <sub>min</sub>				dB
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
<i>f</i> = 900 MHz		-	1.8	-	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
<i>f</i> = 1.8 GHz		-	3	-	

# **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified



Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>				dB	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 900 MHz		-	13	-		
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 1.8 GHz		-	8.5	-		
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,						
<i>f</i> = 900 MHz		-	10.5	-		
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,						
<i>f</i> = 1.8 GHz		-	5	-		
Third order intercept point at output <sup>2)</sup>	IP <sub>3</sub>	-	31	-	dBm	
V <sub>CE</sub> = 8 V, <i>I</i> <sub>C</sub> = 70 mA, <i>f</i> = 0.9 GHz ,						
$Z_{S}=Z_{L}=50\Omega$						
1dB compression point	P <sub>-1dB</sub>	-	22	-		
/ <sub>C</sub> = 70 mA, V <sub>CE</sub> = 8 V, Z <sub>S</sub> =Z <sub>L</sub> =50Ω,						
<i>f</i> = 0.9 GHz						

**Electrical Characteristics** at  $T_A = 25$  °C, unless otherwise specified

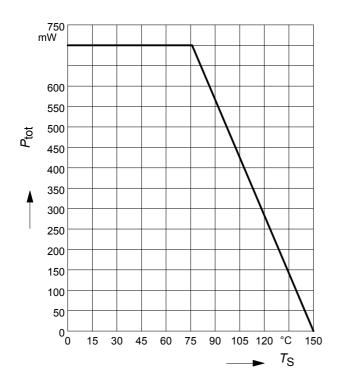
 ${}^{1}G_{ma} = |S_{21e} / S_{12e}| (k - (k^{2} - 1)^{1/2})$ 

 $^{2}IP_{3}$  value depends on termination of all intermodulation frequency components.

Termination used for this measurement is  $50\Omega$  from 0.1 MHz to 6 GHz



# Total power dissipation $P_{tot} = f(T_S)$







## **SPICE GP Model**

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website <u>www.infineon.com/rf.models</u>.

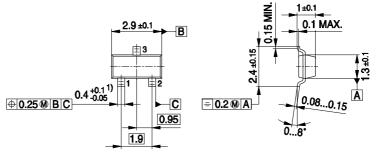
Please consult our website and download the latest versions before actually starting your design.



# **BFR106**



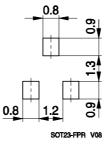




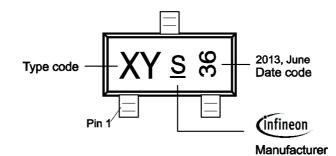
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

## **Foot Print**

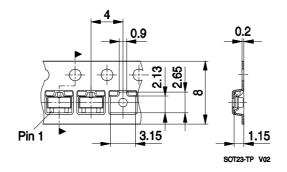


Marking Layout



## **Standard Packing**

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel







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